

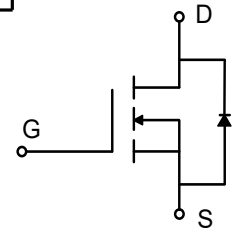
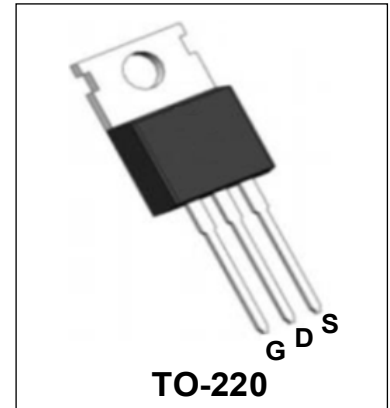
40V N-Channel Enhancement Mode Power MOSFET

Description

WMK80NN04T1 uses advanced power trench technology that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance.

Features

- $V_{DS} = 40V$, $I_D = 80A$
 $R_{DS(on)} < 7m\Omega$ @ $V_{GS} = 10V$
 $R_{DS(on)} < 9.5m\Omega$ @ $V_{GS} = 4.5V$
- High Density Cell Design
- Fully Characterized Avalanche Voltage and Current
- Low $R_{DS(on)}$
- Good Stability and Uniformity with High EAS
- Excellent Package for Good Heat Dissipation



Applications

- Power Management Switches
- DC/DC Converter

Absolute Maximum Ratings ($T_A = 25^\circ C$, unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V_{DS}	40	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current	$T_C = 25^\circ C$	I_D	80	A
	$T_C = 100^\circ C$		51	
Pulsed Drain Current ¹		I_{DM}	320	A
Single Pulse Avalanche Energy ²		EAS	45	mJ
Total Power Dissipation	$T_C = 25^\circ C$	P_D	56.8	W
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	$^\circ C$

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance from Junction-to-Ambient ³	R_{θJA}	60	$^\circ C/W$
Thermal Resistance from Junction-to-Case	R_{θJC}	2.2	$^\circ C/W$

Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise noted)

Parameter		Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics							
Drain-Source Breakdown Voltage		V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	40	-	-	V
Gate-body Leakage current		I _{GSS}	V _{DS} = 0V, V _{GS} = ±20V	-	-	±100	nA
Zero Gate Voltage Drain Current		I _{DSS}	V _{DS} = 40V, V _{GS} = 0V	-	-	1	μA
Gate-Threshold Voltage		V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1	1.7	2.5	V
Drain-Source on-Resistance ⁴		R _{DS(on)}	V _{GS} = 10V, I _D = 30A	-	5.7	7	mΩ
			V _{GS} = 4.5V, I _D = 20A	-	7	9.5	
Forward Transconductance ⁴		g _{fs}	V _{DS} = 10V, I _D = 30A	-	28	-	S
Dynamic Characteristics ⁵							
Input Capacitance		C _{iss}	V _{DS} = 20V, V _{GS} = 0V, f = 1MHz	-	2400	-	pF
Output Capacitance		C _{oss}		-	192	-	
Reverse Transfer Capacitance		C _{rss}		-	140	-	
Gate Resistance		R _g	f =1MHz	-	2.3	-	Ω
Switching Characteristics ⁵							
Total Gate Charge		Q _g	V _{GS} = 10, V _{DS} = 20V, I _D = 30A	-	36	-	nC
Gate-Source Charge		Q _{gs}		-	6.2	-	
Gate-Drain Charge		Q _{gd}		-	7.3	-	
Turn-on Delay Time		t _{d(on)}	V _{GS} = 10V, V _{DD} = 20V, R _G = 3Ω, I _D = 30A	-	9.2	-	ns
Rise Time		t _r		-	12	-	
Turn-off Delay Time		t _{d(off)}		-	45	-	
Fall Time		t _f		-	6.7	-	
Body Diode Reverse Recovery Time		t _{rr}	I _F = 30A, dI/dt = 100A/μs	-	34	-	ns
Body Diode Reverse Recovery Charge		Q _{rr}		-	3.8	-	nC
Drain-Source Body Diode Characteristics							
Diode Forward Voltage ⁴		V _{SD}	I _S = 1A, V _{GS} = 0V	-	-	1.2	V
Continuous Source Current	T _C =25°C	I _S	-	-	-	80	A

Notes:

1. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)} = 150^\circ\text{C}$.
2. The EAS data shows Max. rating . The test condition is $V_{DD} = 25V, V_{GS} = 10V, L = 0.1mH, I_{AS} = 30A$.
3. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
4. The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
5. This value is guaranteed by design hence it is not included in the production test.

Typical Characteristics

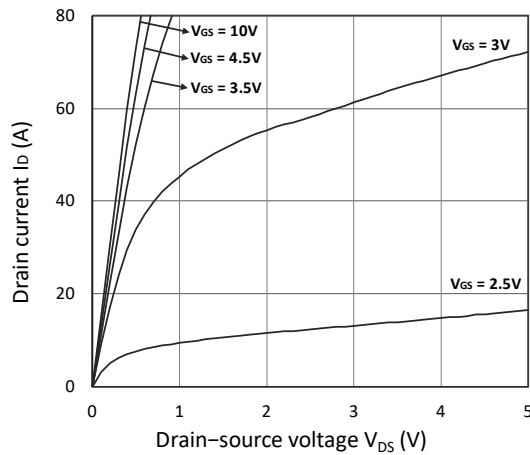


Figure 1. Output Characteristics

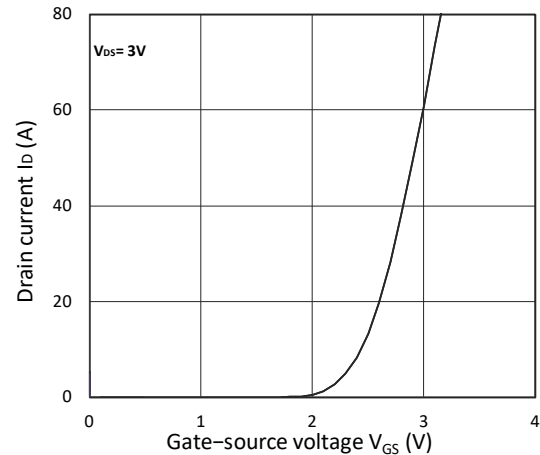


Figure 2. Transfer Characteristics

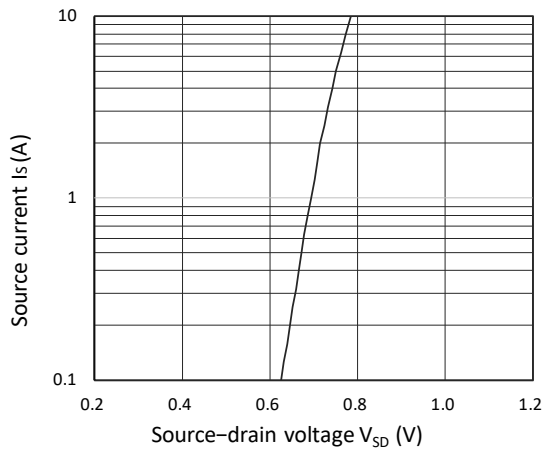
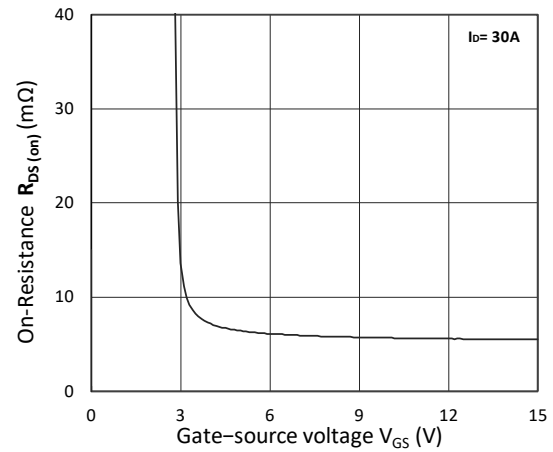
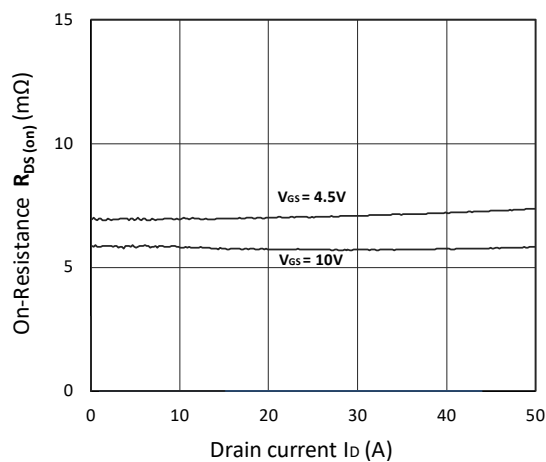
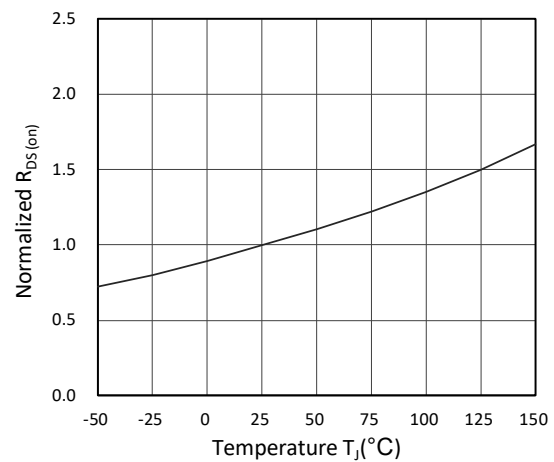


Figure 3. Forward Characteristics of Reverse

Figure 4. $R_{DS(on)}$ vs. V_{GS} Figure 5. $R_{DS(on)}$ vs. I_D Figure 6. Normalized $R_{DS(on)}$ vs. Temperature

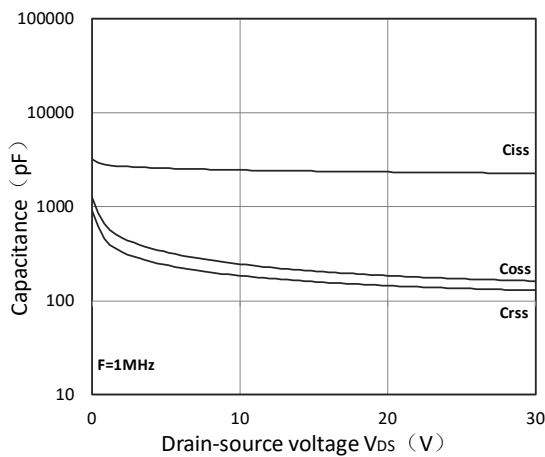


Figure 7. Capacitance Characteristics

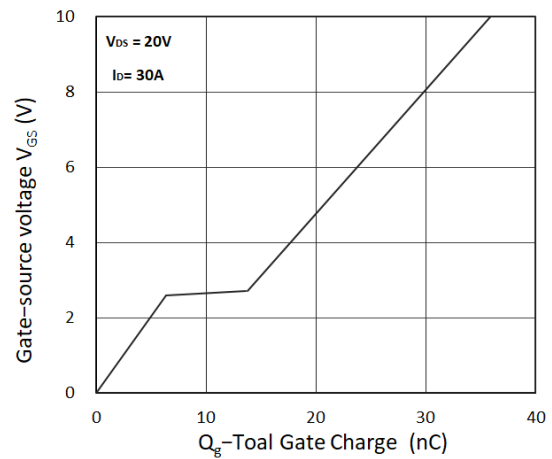


Figure 8. Gate Charge Characteristics

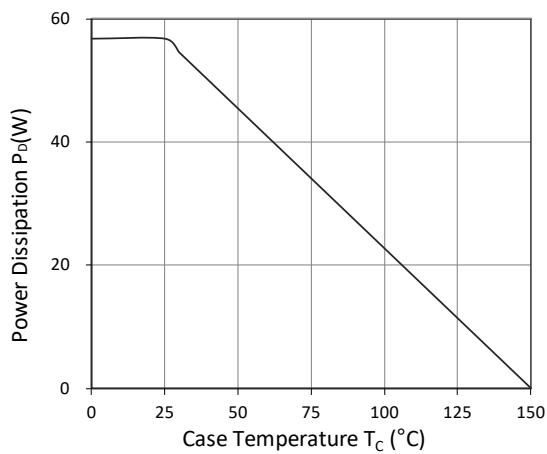


Figure 9. Power Dissipation

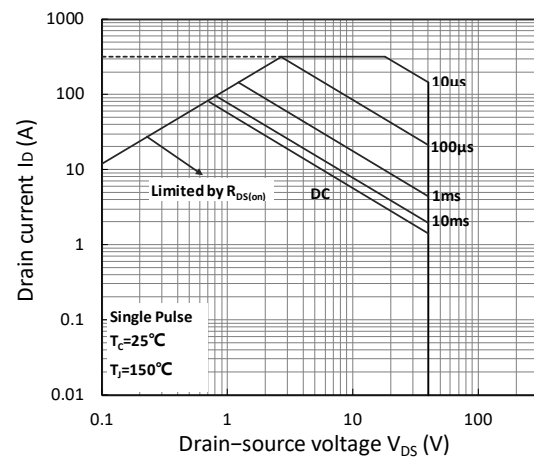


Figure 10. Safe Operating Area

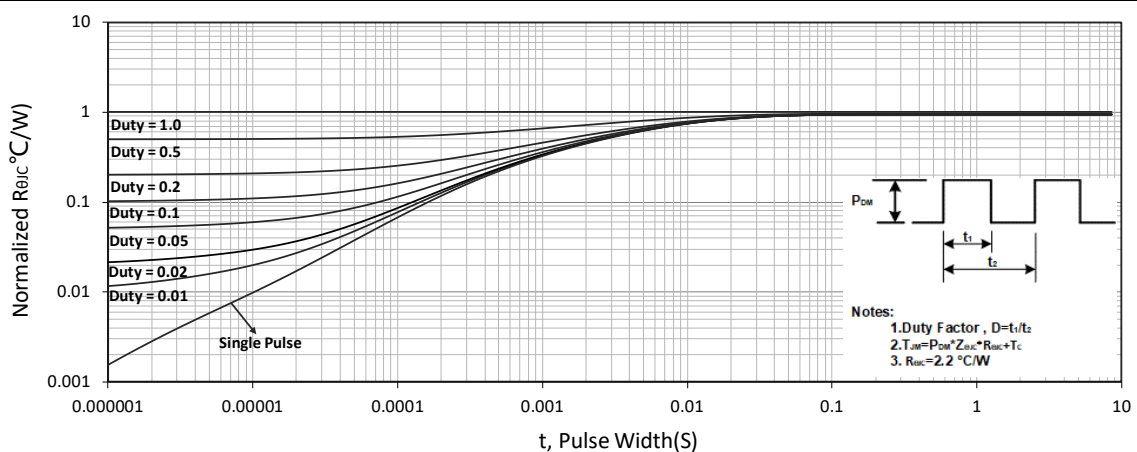


Figure 11. Normalized Maximum Transient Thermal Impedance

Test Circuit

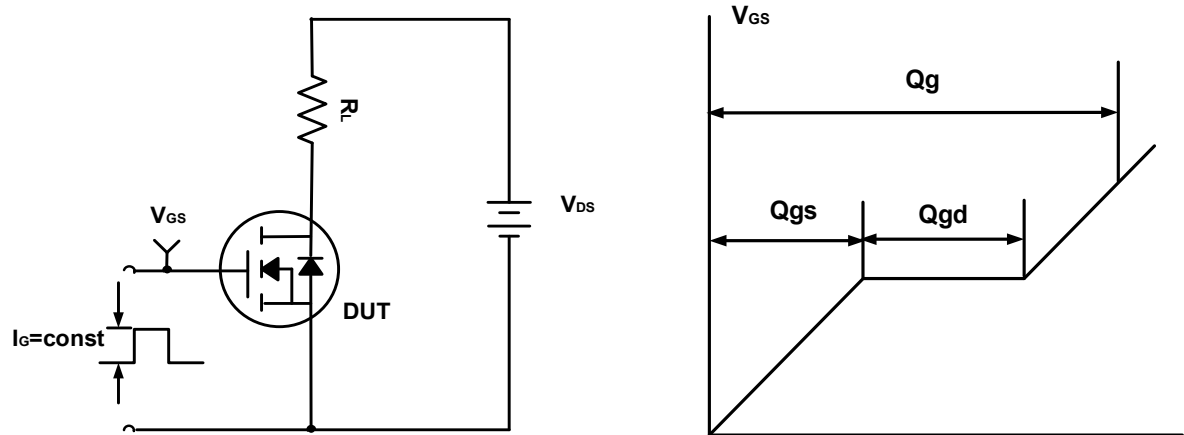


Figure A. Gate Charge Test Circuit & Waveforms

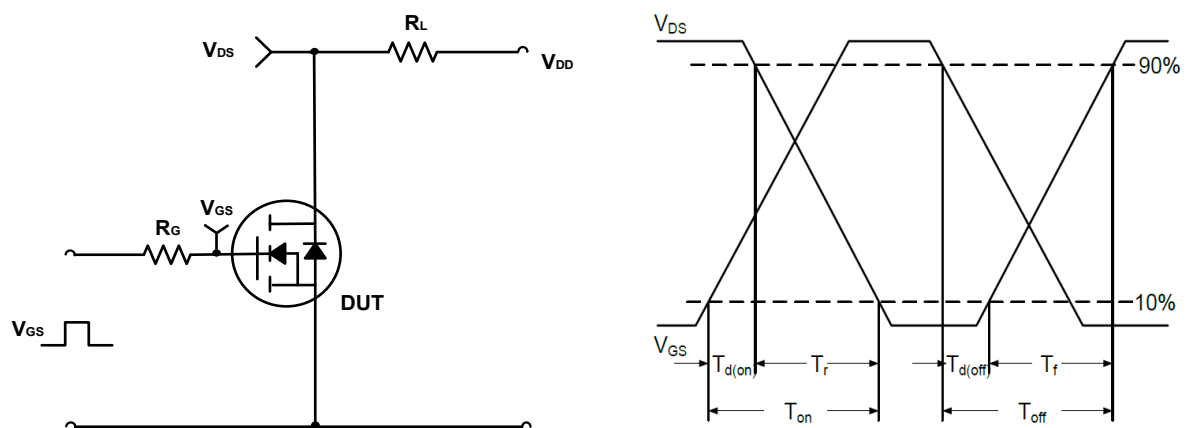


Figure B. Switching Test Circuit & Waveforms

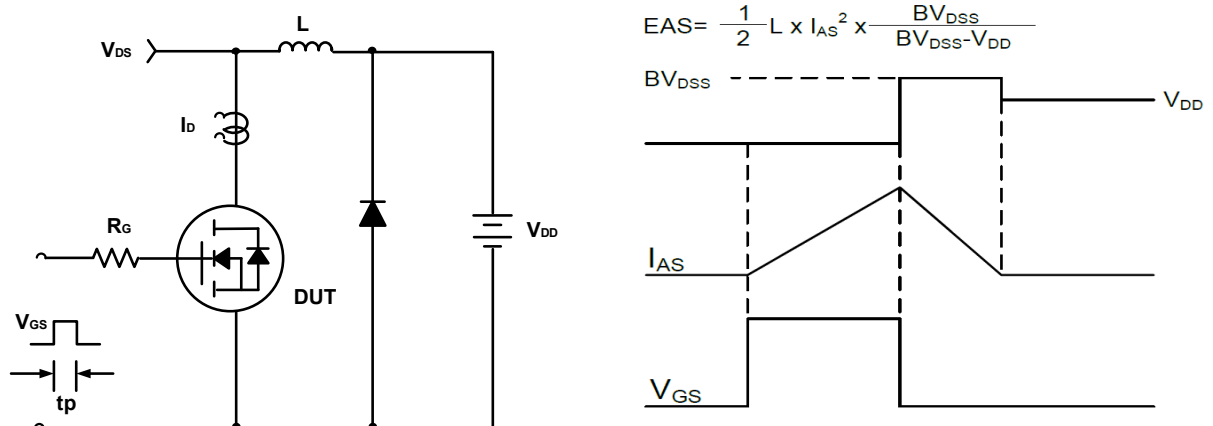
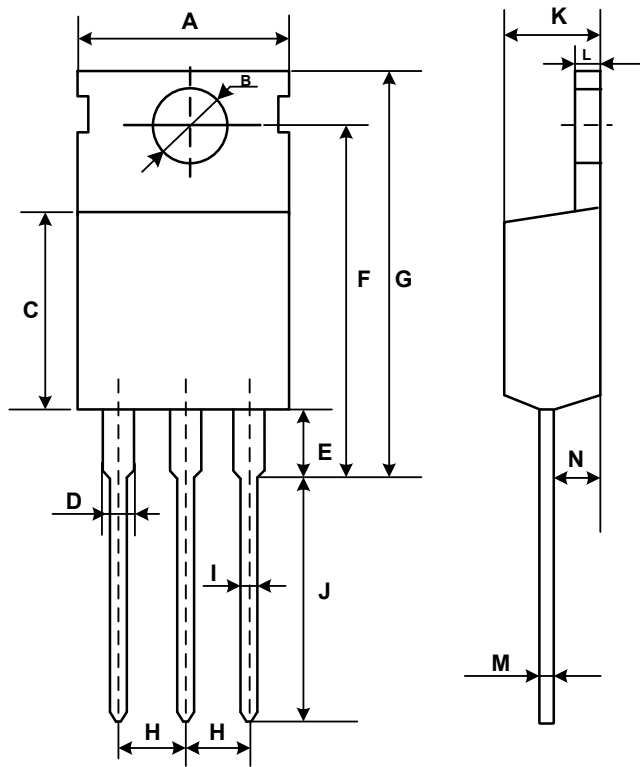


Figure C. Unclamped Inductive Switching Circuit & Waveforms

Mechanical Dimensions for TO-220



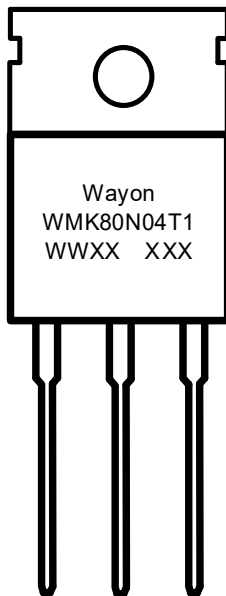
COMMON DIMENSIONS

SYMBOL	MM	
	MIN	MAX
A	9.70	10.30
B	3.40	3.80
C	8.80	9.40
D	1.17	1.47
E	2.60	3.40
F	15.10	16.70
G	19.55MAX	
H	2.54REF	
I	0.70	0.95
J	9.35	11.00
K	4.30	4.77
L	1.20	1.45
M	0.40	0.65
N	2.20	2.60

Ordering Information

Part	Package	Marking	Packing method
WMK80N04T1	TO-220	WMK80N04T1	Tube

Marking Information



WMK80N04T1 = Device code

WWXX XXX= Date code

Contact Information

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